

TSM2312

20V N-Channel MOSFET



SOT-23



Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

Key Parameter Performance

Parameter		Value	Unit	
V_{DS}		20	V	
R _{DS(on)} (max)	$V_{GS} = 4.5V$	33		
	$V_{GS} = 2.5V$	40	mΩ	
	$V_{GS} = 1.8V$	51		
Q _g		11	nC	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

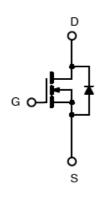
- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing		
TSM2312CX RFG	SOT-23	3,000pcs / 7" Reel		

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (T_C = 25°C, unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	±8	V	
Continuous Drain Current		I _D	4.9	Α	
Pulsed Drain Current (Note 1)		I _{DM}	15	А	
Continuous Source Current (Diode Conduction) (Note 2)		I _S	1.0	А	
Maximum Power Dissipation	Ta = 25°C		0.75	W	
	Ta = 75°C	P _D	0.48		
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit	
Thermal Resistance Junction to Lead	$R_{\Theta JL}$	75	°C/W	
Thermal Resistance Junction to Ambient	R _{OJA}	140	°C/W	





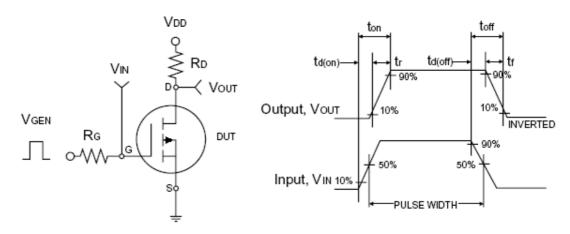
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Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static ^(Note 3)		•			•	
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.45	0.65	1.0	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I _{DSS}			1.0	μA
On-State Drain Current	$V_{DS} = 10V, V_{GS} = 4.5V$	I _{D(ON)}	15			Α
	$V_{GS} = 4.5V, I_D = 4.9A$			27	33	mΩ
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 4.4A$	R _{DS(ON)}		33	40	
	$V_{GS} = 1.8V, I_D = 3.9A$			42	51	
Forward Transconductance	$V_{DS} = 15V, I_{D} = 5.0A$	g _{fs}		40		S
Diode Forward Voltage	$I_S = 1.0A, V_{GS} = 0V$	V_{SD}		0.8	1.2	V
Dynamic ^(Note 4)						
Total Gate Charge	$V_{DS} = 10V, I_{D} = 5.0A,$ $V_{GS} = 4.5V$	Q_g		11	14	nC
Gate-Source Charge		Q_gs		1.5		
Gate-Drain Charge		Q_{gd}		2.1		
Input Capacitance	.,	C_{iss}		500		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C_{oss}		300		pF
Reverse Transfer Capacitance		C_{rss}		140		
Switching ^(Note 5)						
Turn-On Delay Time	$V_{DD} = 10V, R_L = 10\Omega,$ $I_D = 1A, V_{GEN} = 4.5V,$ $R_G = 6\Omega$	t _{d(on)}		15	25	
Turn-On Rise Time		t _r		40	60	
Turn-Off Delay Time		t _{d(off)}		48	70	ns
Turn-Off Fall Time		t _f		31	45	

Notes:

- 1. Pulse width limited by the maximum junction temperature
- 2. Surface Mounted on FR4 Board t ≤ 5 sec.
- 3. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



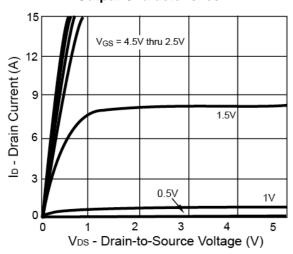
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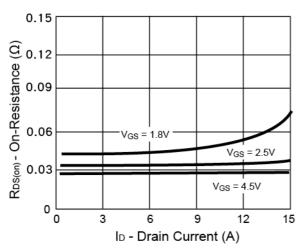


Electrical Characteristics Curve

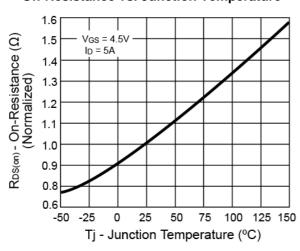
Output Characteristics



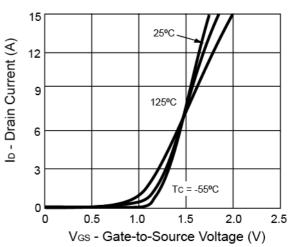
On-Resistance vs. Drain Current



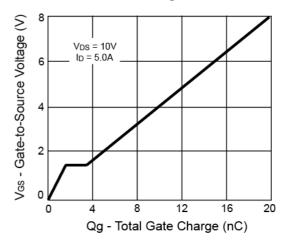
On-Resistance vs. Junction Temperature



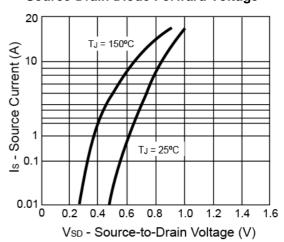
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



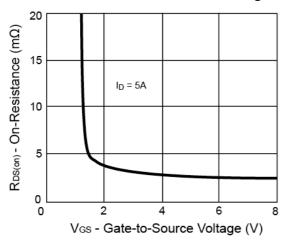
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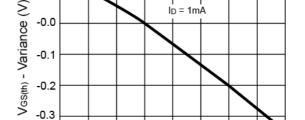
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Electrical Characteristics Curve

On-Resistance vs. Gate-Source Voltage





Threshold Voltage

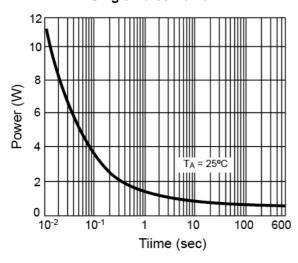
0.2

0.1

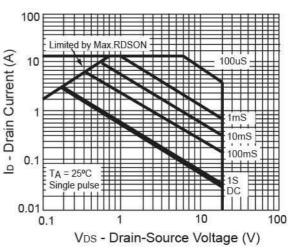
-0.4 L -50

-25 0 25 50 75 100 125 150 Tj - Junction Temperature (°C)

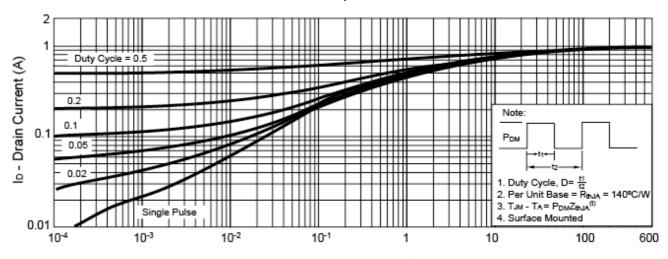
Single Pulse Power



Safety Operation Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

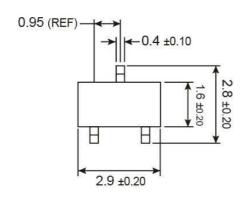


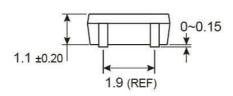
Square Wave Pulse Duration (sec)

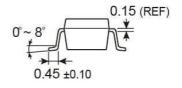




SOT-23 Mechanical Drawing

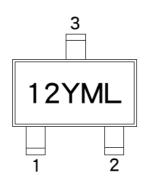






Unit: Millimeters

Marking Diagram



12 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



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